Am7202-40/50/65/80

High Density First-in First-out (FIFO) 1024x9 CMOS Memory



DISTINCTIVE CHARACTERISTICS

- · RAM based FIFO
- · 1024x9 organization
- Cycle times of 50/65/80/100 nanoseconds
- Asynchronous and simultaneous writes and reads
- · Low power consumption
 - 90 mA max, -50/65/80
 - 100 mA max, -40

- · Status flags full, half-full, empty
- Retransmit capability
- · Expandable in both width and depth
- · Increased noise immunity for XI CMOS threshold
- Functional and pin compatible with industry standard devices

GENERAL DESCRIPTION

The Am7202 is a RAM-based CMOS FIFO that is 1024 words deep with 9-bit wide words. It is expandable to any width and/or depth to create much larger FIFOs.

This FIFO can accept data and output data asynchronously and simultaneously at data rates from 0 to 20 MHz. Status flags are provided to signify empty, full, and half-full conditions. The capability also exists to retransmit data from the FIFO. High-density FIFOs such as the Am7202 are useful in a wide range of applications. The ability to buffer large transfers of data and the rate adaption capabilities make the Am7202 useful in communication, image processing, mass storage, DSP, and printing systems.

BLOCK DIAGRAM

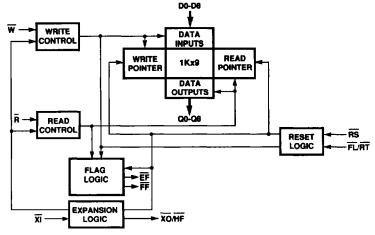
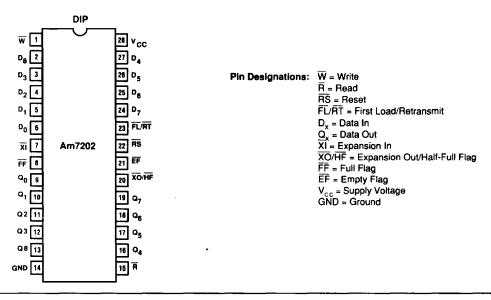


Figure 1.

This document contains information on a product under development at Advanced Micro Devices, inc. The information is intended to help you to evaluate this product. AMD reserves the right to change or discontinue work on this proposed product without notice. Publication # Ray. Amendment 10909 B /0 Issue Date: February 1989

CONNECTION DIAGRAMS

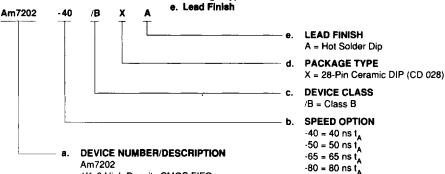


MILITARY ORDERING INFORMATION

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of:

- a. Device Number
- b. Speed Option (if applicable) c. Device Class
- d. Package Type



1Kx9 High Density CMOS FIFO

Valid Com	binations
Am7202-40	
Am7202-50	
Am7202-65	/BXA
Am7202-80	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

Group A Tests

Group A Tests consist of subgroups 1, 2, 3, 7, 8, 9, 10, 11.

Military burn-in is in accordance with the current revision of MIL-STD-883, Test Method 1015, Conditions A through E. Test conditions are selected at AMD's option.

MILITARY BURN-IN

ABSOLUTE MAXIMUM RATINGS

Supply voltage, V.c	0.5 V to + 7.0 V
Input voltage	0.5 V to V _{cc} + 0.5 V
Operating temperature	55°C to +125°C
Storage temperature	
Power dissipation	2.0 W
DC output current	

Stresses above those listed under ABSOLUTE MAXIMUM RAT-INGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability. Absolute maximum ratings are for system design reference; parameters given are not tested.

DC CHARACTERISTICS Military: V_{cc} = 5 V ± 10%, T_A^{\dagger} = -55°C to + 125°C

Parameter Symbol	Parameter Description		202-40 40 ns Max.		202-50 50 ns Max.		02-65 65 ns Max.		202-80 80 ns Max.	Unit
I _{IL}	Input Leakage Current (any input) (Note 1)	-10	10	-10	10	-10	10	-10	10	μА
l _{io}	Output Leakage Current (data outputs) (Note 2)	-10	10	-10	10	-10	10	-10	10	μА
V _{IH}	Input High Voltage (all inputs except XI) (Note 3)	2.2	-	2.2	_	2.2	-	2.2	-	٧
V _{IL}	Input Low Voltage (all inputs except XI) (Note 3)	-	0.8	_	0.8	_	0.8	-	8.0	V
V _{iHXI}	Input High Voltage, XI (Note 3)	3.5	-	3.5	_	3.5	_	3.5	_	٧
V _{ILXI}	Input Low Voltage, XI (Note 3)	_	1.5	-	1.5	_	1.5	-	1.5	V
V _{oh}	Output Logic "1" Voltage 1 _{OH} = -2 mA	2.4	_	2.4	_	2.4	-	2.4	-	٧
V _{oL}	Output Logic "0" voltage I _{OL} = 8 mA	-	0.4	-	0.4		0.4	_	0.4	\ v
1001	Average V _{cc} Power Supply Current (Note 4)	T -	100	_	90	_	90	-	90	mA
I _{CC2}	Average Standby Current (R = W = RS = FL/RT = V _{IH}) (Note 4)	-	25	_	25	_	25	-	25	mA
I _{ccs}	Power Down Current (all inputs = V _{cc} -0.2 V) (Note 4)	-	5	-	5	-	5	_	5	mA

- Notes: 1. Measurements with GND $\leq V_{IN} \leq V_{CC}$.
 - 2. R≥ V_{IH}, GND ≤ V_{OUT} ≤ V_{CC}.
 - 3. V_{IL} and V_{IH} are input conditions of output tests and are not themselves directly tested. V_{IL} and V_{IH} are absolute voltages with respect to device ground and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.
 - 4. I_{cc} measurements are made with outputs open.
 - † Instant-On Case Temperature.

AC CHARACTERISTICS V_{cc} = 5 V \pm 10%, T_A^{\dagger} = -55°C to + 125°C

Parameter			7202-40		7202-50	1	7202-65		7202-80	
Symbol	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Write and	Flag Timing									
t _{wc}	Write Cycle Time	50		65		80		100		ns
twew	Write Pulse Width	40		50		65		80		ns
t _{wn}	Write Recovery Time	10	-	15		15		20		ns
t _{os}	Data Setup Tirne	20		30		30		40		ns
t _{DH}	Data Hold Time	0		5		10		10		ns
t _{wff}	Write LOW to Full Flag LOW		35	<u> </u>	45	<u> </u>	60		60	ns
twhe	Write LOW to Half-Full Flag LOW		50	l _	65		80		100	ns
twer	Write HIGH to Empty Flag HIGH		35		45		60		60	ns
t _{wLZ}	Write pulse HIGH to data bus at LOW Z (Note 1)	10		15		15		15		ns
Read and	Flag Timing									
t _{ec}	Read Cycle Time	50		65		80		100		ns
t _A	Access Time		40		50		65		80	ns
t _{an}	Read Recovery Time	10		15		15		20		ns
t _{apw}	Read Pulse Width	40		50		65		80		ns
t _{mtZ}	Read pulse LOW to data bus at LOW Z (Note 1)	5		10		10		10		ns
t _{ov}	Data Valid from read pulse HIGH	5		5		5		5		ns
t _{RHZ}	Read pulse HIGH to data bus at HIGH Z (Note 1)		25		30		30		30	ns
t _{nee}	Read HIGH to Full Flag HIGH		35		45		60		60	ns
t _{ene}	Read HIGH to Half Full-Flag HIGH		50		65		80		100	ns
t _{REF}	Read LOW to Empty Flag LOW		30		45		60		60	ns
Reset Tim	ing	•								
t _{esc}	Reset Cycle Time	50		65		80		100		ns
t _{RS}	Reset Pulse Width	40		50		65		80		ns
t _{ess}	Reset Setup Time	40		50		65		80		ns
t _{ese}	Reset Recovery Time	10		15		15		20		ns
t _{ef}	Reset to Empty Flag LOW		50		65		80	<u> </u>	100	ns
t _{efe}	Reset to Half-Full Flag High		50		65		80		100	ns
t _{FFH}	Reset to Full Flag HIGH		50	T	65		80		100	ns
Retransm	it Timing									
t _{etc}	Retransmit Cycle Time	50		65		80		100		ns
t _{RT}	Retransmit Pulse Width	40		50		65		80		ns
t _{ere}	Retransmit Recovery Time	10		15		15		20		ns

Note: 1. Characterized parameters.

[†] Instant-On Case Temperature.